

IN THE SPECIFICATION:

Replace the paragraph at page 23, line 20, with the following rewritten paragraph:

A1 Next, the amorphous silicon film 18 is formed in a 10 nm-thick on the polycrystalline silicon film 16 by, e.g., CVD method (FIG. 6D). At this time, a native oxide film 17 is formed between the polycrystalline silicon film 16 and the amorphous silicon film 18.

Replace the paragraph at page 29, line 5, with the following rewritten paragraph:

A2
A.M.
12/09/02
Next, a 10 nm-thick amorphous silicon film 18 is formed on the polycrystalline silicon film 40 by, e.g., CVD method (FIG. 11A). At this time, a native oxide film 17 is present between the polycrystalline silicon film 40 and the amorphous silicon film 18.

IN THE CLAIMS:

AMEND claims 1 and 2 as follows:

- Sub
/C1
A3
1. (Amended) A semiconductor device comprising:
a pair of impurity diffused regions formed in a silicon substrate, spaced from each other; and
a gate electrode formed above the silicon substrate between the pair of impurity diffused regions
with a gate insulation film interposed therebetween, the gate electrode being formed of a first polycrystalline silicon film formed on the gate insulation film, a second polycrystalline silicon film formed on the first polycrystalline silicon film having a thickness thinner than that of the first polycrystalline silicon film and